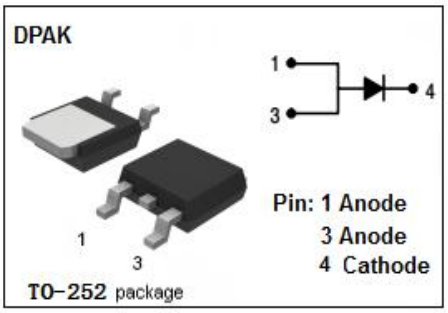
Schottky Barrier Rectifier

MBRD835

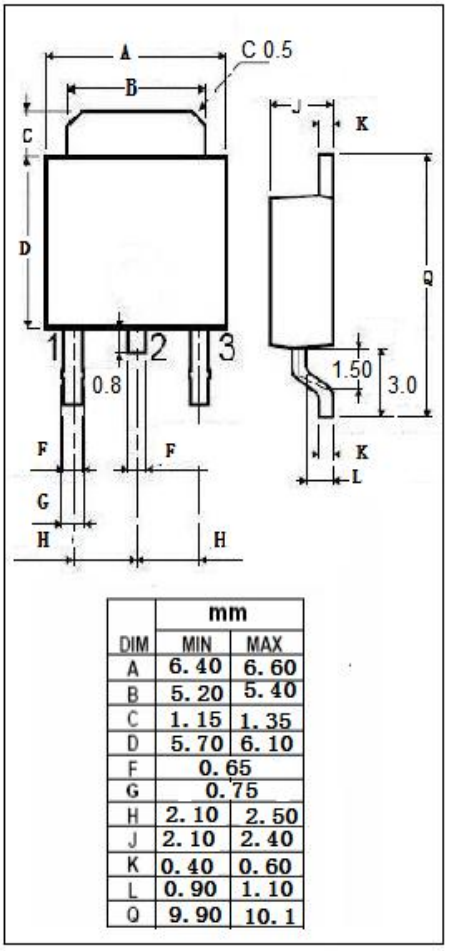


FEATURES

- Schottky barrier chip
- Low Power Loss,High Efficiency
- Guard ring for transient protection
- High Operating Junction Temperature
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For use in high frequency rectifier of switching mode power supplies,freewheeling diodes,DC-to-DC converters or polarity protection application.



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RMS} V_R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	35	V
$I_{F(AV)}$	Average Rectified Forward Current	8	A
I_{FSM}	Non-repetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	175	A
T_J	Junction Temperature	-65~125	℃
T_{stg}	Storage Temperature Range	-65~150	℃

Schottky Barrier Rectifier MBRD835

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.8	℃/W

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	I_F = 8A ; Tj=25℃		0.51	V
		I_F = 8A ; Tj= 125℃		0.41	
I_R	Maximum Instantaneous Reverse Current	V_R= $V_{RRM;}$Tj= 25℃		1.4	mA
		V_R= $V_{RRM;}$Tj= 100℃		35	